DOCUMENT CHANGE REQUEST

DCR number 226

Changes required for: N/A

Originator: Carol Brooks

Date: 2005/12/20

Date sent: 2005/12/20

Organisation:

Status: IMPLEMENTED

Title:	Advanced CMOS Quad 2-Input NAND Gates, based on type 54AC00		
Number:	9201/125	Issue:	2

Other documents affected:

9201/126-2, 9201/127-2, 9201/138-2, 9201/139-2, 9408/063-2

Page:

See below

Paragraph:

See below

Original wording:

Proposed wording:

Para 2.6.1 and 2.6.2, page 17, Notes 1 and 2 - the minimum resistor value is 200 ohms

Para 2.7, page 18, The test condition for Output is Open; the input(s) are at Vgen; the pulse frequency test condition for Tr=Tf is less than or equal to 8ns/V; for Notes 1 and 2 - the minimum resistor value is 200 ohms.

Para 2.9.1 becomes:

Continuous bias shall be applied during irradiation testing as specified below.

The total dose level appolied shall be as specified in the component type variant information herein or in the Purchase Order.

Para 2.9.1.1 and 2.9.1.2 are deleted. The table in to 2.9.1.1 becomes part of 2.9.1 with the following modifications:

Add (Note 1) to the column heading Test Conditions.

The Test Condition for Inputs becomes Note 2.

Note 2 is "Vin such that Vout=0 with a maximum input at Vdd.

Justification:

This DCR reflects the changes recommended by STMicroelectronis to reflect the actual test conditions used for their product.

Attachments:
N/A
Modifications:
N/A
Approval signature:
Date signed:
2005-12-20